

Claim 1
Claim 3

5 a conductive wire comprising at least a first contact end and a second contact end, the first contact end electrically connecting with a gate electrode on the top of the MOS transistor, and the second contact end electrically connecting with a doped region in the substrate; and

10 a fusion area positioned in the conductive wire to disconnect the conductive wire and the MOS transistor, the fusion area comprising polysilicon; wherein ions in the gate oxide are transmitted to the doped region via the conductive wire so as to reduce plasma damage to the gate oxide.

15 Claim 4 is canceled.

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